PHILIPS INTERNATIONAL 56E D 7110826 0043248 923 PHIN

SILICON DARLINGTON POWER TRANSISTORS

T-33-3/

PNP silicon darlington power transistors in a SOT186 envelope with an electrically insulated mounting base. The devices are designed for audio output stages and general amplifier and switching applications. NPN complements are BDT63F, BDT63AF, BDT63BF and BDT63CF.

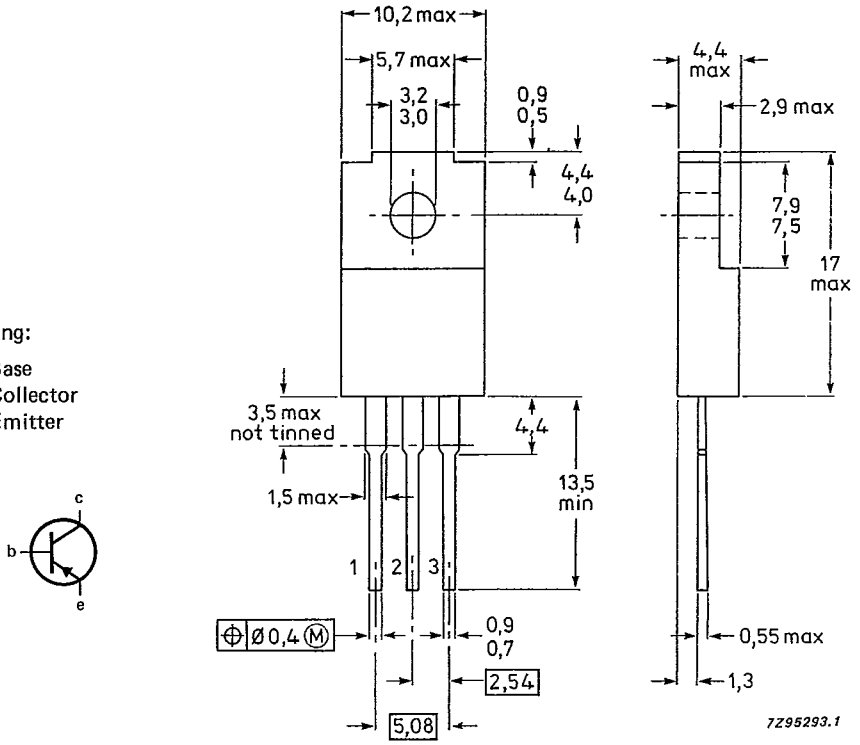
QUICK REFERENCE DATA

			BDT62F	62AF	62BF	62CF	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	60	80	100	120	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	60	80	100	120	V
Collector current DC	$-I_C$	max.		10			A
Total power dissipation up to T_h = 25 °C	P_{tot}	max.		36			W
Junction temperature	T_j	max.		150			°C
DC current gain $-I_C$ = 3 A; $-V_{CE}$ = 3 V	h_{FE}	min.		1000			

MECHANICAL DATA

Dimensions in mm

Fig.1 SOT186.



Pinning:

1 = Base
2 = Collector
3 = Emitter

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RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BDT62F	62AF	62BF	62CF	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	60	80	100	120	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	60	80	100	120	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.		5.0			V
Collector current							
DC	$-I_C$	max.		10			A
peak value	$-I_{CM}$	max.		15			A
Base current (DC)	$-I_B$	max.		250			mA
Total power dissipation							
up to T_h = 25 °C (1)	P_{tot}	max.		21			W
up to T_h = 25 °C (2)		max.		36			W
Storage temperature	T_{stg}			−65 to 150			°C
Junction temperature	T_j	max.		150			°C

THERMAL RESISTANCE

From junction to internal heatsink	$R_{th\ j\text{-}mb}$	=	1.17	K/W
From junction to external heatsink (1)	$R_{th\ j\text{-}h}$	=	5.95	K/W
From junction to external heatsink (2)	$R_{th\ j\text{-}h}$	=	3.47	K/W

INSULATION

Voltage allowed between all terminals and external heatsink, peak value	V_{insul}	max.	1000	V
Insulation capacitance from collector to external heatsink	C_{th}	typ.	12	pF

(1) Mounted without heatsink compound and 30 ± 5 newton pressure on centre of envelope.

(2) Mounted with heatsink compound and 30 ± 5 newton pressure on centre of envelope.

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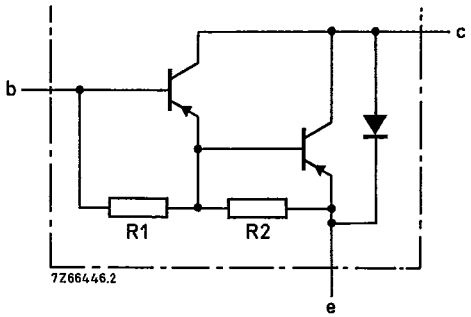

R1 typ. 4 kΩ
R2 typ. 60 Ω

Fig. 2 Circuit diagram.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
$I_E = 0$; $-V_{CB} = -V_{CBOmax}$	$-I_{CBO}$	max.	0.2	mA
$I_E = 0$; T_j = 150 °C; $-V_{CB} = -1/2\ V_{CBOmax}$	$-I_{CBO}$	max.	2.0	mA
$I_B = 0$; $-V_{CE} = -1/2\ V_{CEOmax}$	$-I_{CEO}$	max.	0.5	mA
Emitter cut-off current				
$I_C = 0$; $-V_{EB}$ = 5 V	$-I_{EBO}$	max.	5.0	mA
Forward bias second-breakdown collector current $-V_{CE}$ = 40 V; t = 0.1 s; non-repetitive (without heatsink)	$I_{(SB)}$	min.	0.9	A
DC current gain (3)				
$-I_C$ = 3 A; $-V_{CE}$ = 3 V	h_{FE}	min.	1000	
$-I_C$ = 10 A; $-V_{CE}$ = 3 V	h_{FE}	typ.	150	
Base-emitter voltage (3)				
$-I_C$ = 3 A; $-V_{CE}$ = 3 V	$-V_{BE}$	max.	2.5	V
Collector-emitter saturation voltage (3)				
$-I_C$ = 3 A; $-I_B$ = 12 mA	$-V_{CEsat}$	max.	2.0	V
$-I_C$ = 8 A; $-I_B$ = 80 mA	$-V_{CEsat}$	max.	2.5	V
Cut-off frequency				
$-I_C$ = 3 A; $-V_{CE}$ = 3 V	f_{hfe}	typ.	100	kHz
Collector capacitance				
$-V_{CB}$ = 10 V; f = 1 MHz	C_c	typ.	100	pF
Small-signal current gain at f = 1 MHz				
$-I_C$ = 3 A; $-V_{CE}$ = 3 V	h_{fe}	min.	10	
Diode, forward voltage				
I_F = 3 A	V_F	max.	2.0	V

(3) Measured under pulse conditions; $t_p < 300\ \mu s$; $\delta < 2\%$.

CHARACTERISTICS (continued)

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Switching times (between 10% and 90% levels) $-I_{Con} = 3$ A; $-I_{Bon} = I_{Boff} = 12$ mA				
Turn-on time	t_{on}	typ.	0.5	μs
		max.	1.5	μs
Turn-off time	t_{off}	typ.	2.5	μs
		max.	5.0	μs

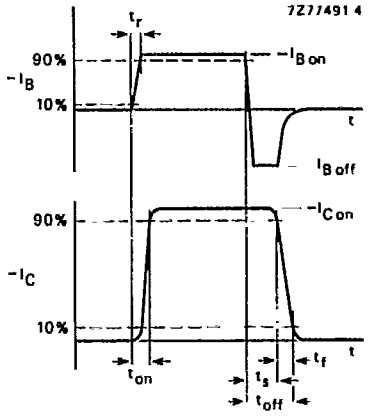
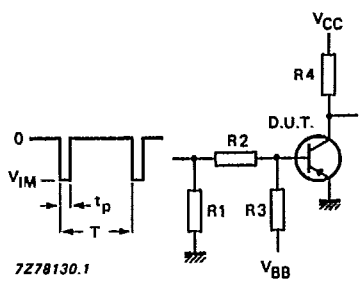


Fig. 3 Switching times waveforms.



$-V_{IM}$	= 10 V
$-V_{CC}$	= 10 V
$+V_{BB}$	= 4.0 V
R1	= 56 Ω
R2	= 410 Ω
R3	= 560 Ω
R4	= 3.0 Ω
$t_r = t_f$	= 15 ns
t_p	= 10 μs
T	= 500 μs

Fig. 4 Switching times test circuit.

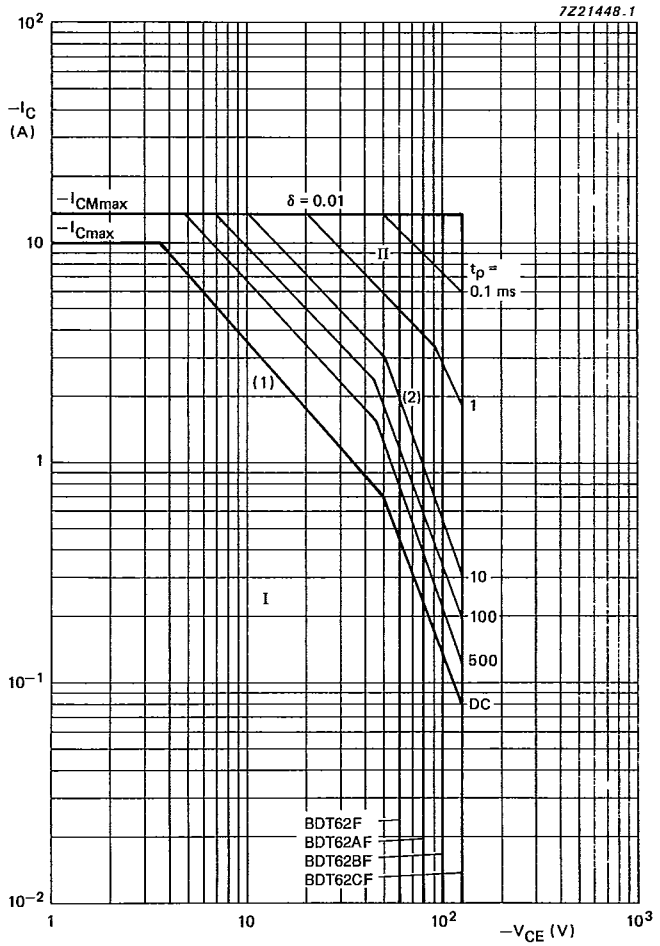


Fig. 5 Safe Operating Area; T_h = 25 °C.

I Region of permissible DC operation.

II Permissible extension for repetitive pulse operation.

(1) $P_{tot\ max}$ and $P_{peak\ max}$ lines.

(2) Second-breakdown limits.

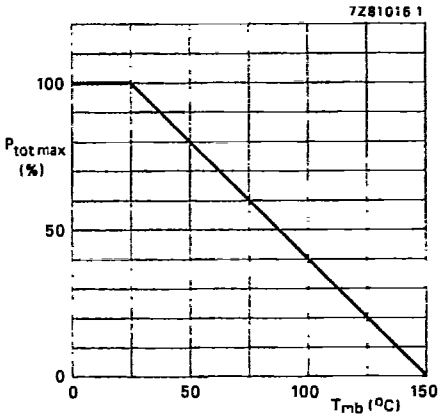


Fig. 6 Power derating curve.

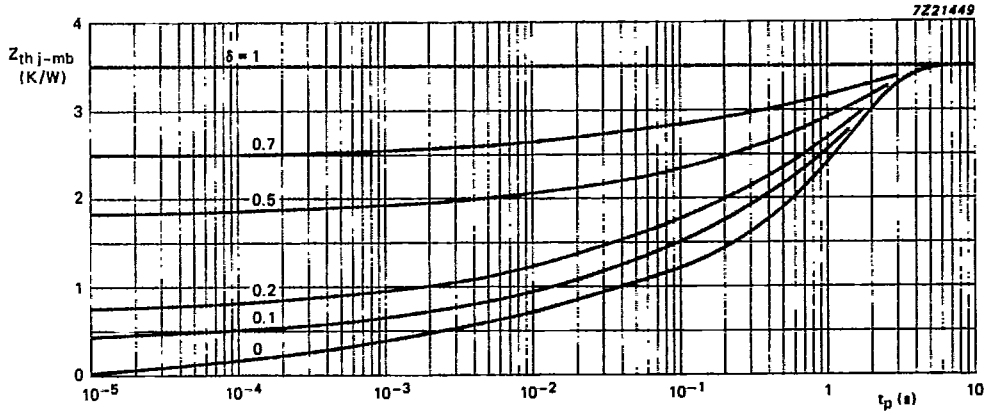


Fig. 7 Pulse power rating chart.

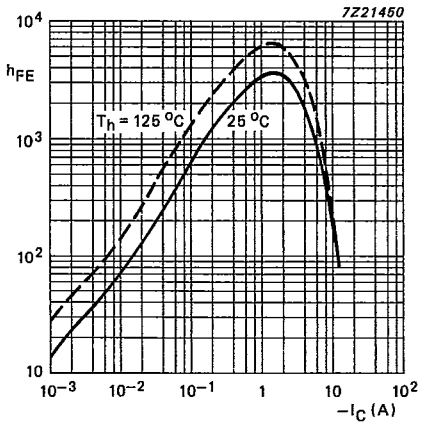


Fig. 8 Typical DC current gain at $-V_{CE}$ = 3 V.

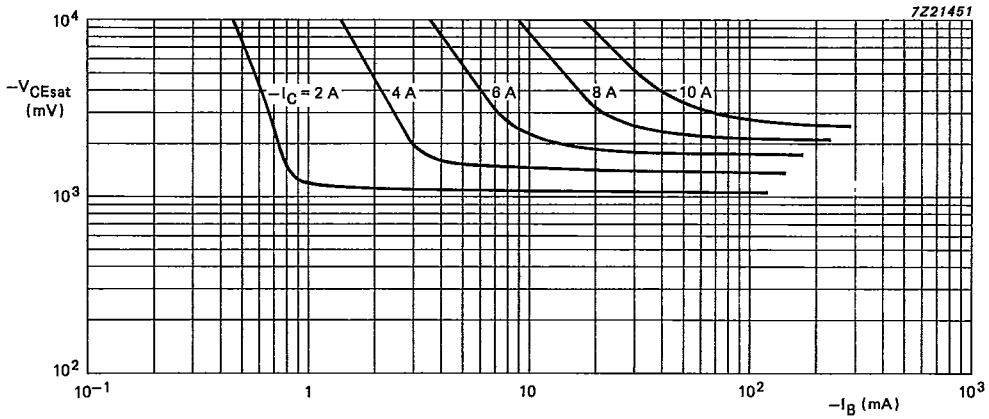


Fig. 9 Typical collector-emitter saturation voltage; T_h = 25 °C.